



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

2SC1815

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

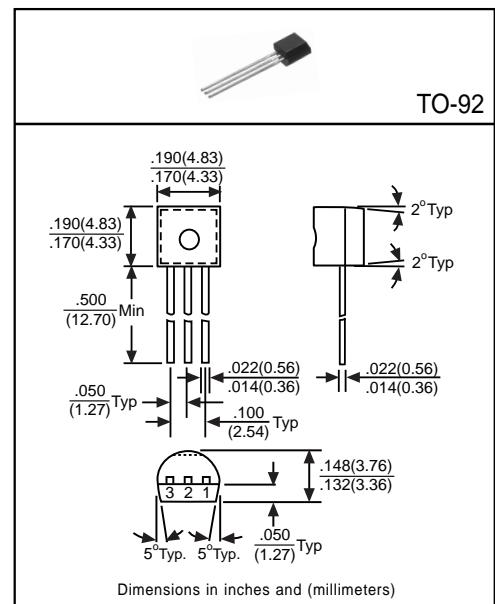
Designed for use in driver stage of AF amplifier
general purpose amplification.

Pinning

- 1 = Emitter
- 2 = Collector
- 3 = Base

Absolute Maximum Ratings($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	50	mA
Total Power Dissipation	P_D	400	mW
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^\circ\text{C}$



Dimensions in inches and (millimeters)

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Volatge	BV_{CBO}	60	-	-	V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	-	-	V	$I_C=1\text{mA}, I_B=0$
Emitter-Base Breakdown Volatge	BV_{EBO}	5	-	-	V	$I_E=10\mu\text{A}, I_C=0$
Collector Cutoff Current	I_{CBO}	-	-	100	nA	$V_{CB}=60\text{V}, I_E=0$
Emitter Cutoff Current	I_{EBO}	-	-	100	nA	$V_{EB}=5\text{V}, I_C=0$
Collector-Emitter Saturation Voltage ⁽¹⁾	$V_{CE(\text{sat})}$	-	-	0.25	V	$I_C=100\text{mA}, I_B=10\text{mA}$
Base-Emitter Saturation Voltage ⁽¹⁾	$V_{BE(\text{sat})}$	-	-	1	V	$I_C=100\text{mA}, I_B=10\text{mA}$
DC Current Gain ⁽¹⁾	h_{FE1}	70	-	700	-	$I_C=2\text{mA}, V_{CE}=6\text{V}$
	h_{FE2}	25	-	-	-	$I_C=150\text{mA}, V_{CE}=6\text{V}$
Transition Frequency	f_T	80	-	-	MHz	$I_C=1\text{mA}, V_{CE}=10\text{V}$
Output Capacitance	C_{ob}	-	-	3.5	pF	$V_{CB}=10\text{V}, f=1\text{MHz}, I_E=0$

(1)Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$ Classification of h_{FE1}

Rank	O	Y	GR	BL
Range	70~140	120~240	200~400	350~700